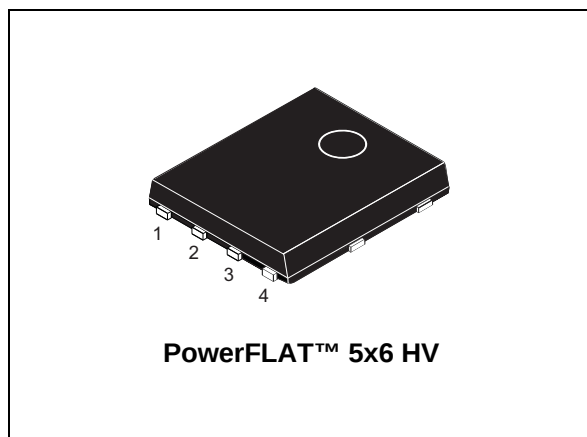


N-channel 650 V, 0.365 Ω typ., 6.5 A MDmesh™ M2 Power MOSFET in a PowerFLAT™ 5x6 HV package

Datasheet – production data



Features

Order code	V _{DS}	R _{DS(on)} max	I _D
STL13N65M2	650 V	0.475 Ω	6.5 A

- Extremely low gate charge
- Excellent output capacitance (C_{OSS}) profile
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using MDmesh™ M2 technology. Thanks to its strip layout and an improved vertical structure, the device exhibits low on-resistance and optimized switching characteristics, rendering it suitable for the most demanding high efficiency converters.

Figure 1. Internal schematic diagram

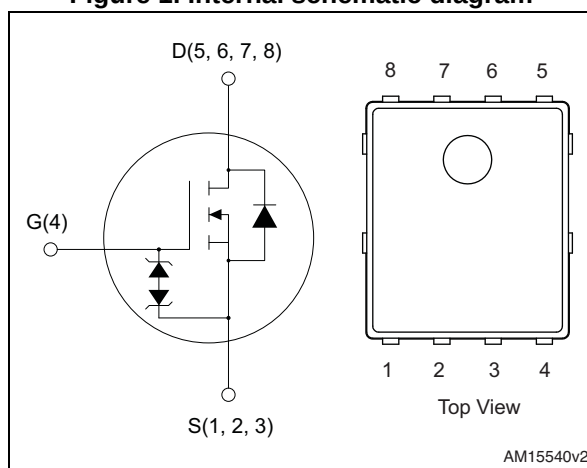


Table 1. Device summary

Order code	Marking	Package	Packaging
STL13N65M2	13N65M2	PowerFLAT™ 5x6 HV	Tape and reel

Contents

1 **Electrical ratings** 3

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3 **Test circuits** 8

4 **Package mechanical data** 9

5 **Packaging mechanical data** 13

6 **Revision history** 15



1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 25	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^{\circ}\text{C}$	6.5	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^{\circ}\text{C}$	4.1	A
$I_{DM}^{(1)}$	Drain current (pulsed)	26	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^{\circ}\text{C}$	52	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(3)}$	MOSFET dv/dt ruggedness	50	V/ns
T_{stg}	Storage temperature	- 55 to 150	$^{\circ}\text{C}$
T_j	Max. operating junction temperature	150	

1. Pulse width limited by safe operating area.
2. $I_{SD} \leq 6.5\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$; $V_{DS\text{ peak}} < V_{(BR)DSS}$, $V_{DD}=400\text{ V}$.
3. $V_{DS} \leq 520\text{ V}$

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	2.4	$^{\circ}\text{C}/\text{W}$
$R_{thj-pcb}$	Thermal resistance junction-pcb max ⁽¹⁾	59	$^{\circ}\text{C}/\text{W}$

1. When mounted on 1 inch² FR-4, 2 Oz copper board

Table 4. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by T_{jmax})	1.5	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25\text{ }^{\circ}\text{C}$, $I_D = I_{AR}$; $V_{DD} = 50\text{ V}$)	110	mJ

2 Electrical characteristics

($T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Table 5. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$	650			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 650\text{ V}$			1	μA
		$V_{GS} = 0\text{ V}$, $V_{DS} = 650\text{ V}$, $T_C = 125\text{ }^{\circ}\text{C}$			100	μA
I_{GSS}	Gate-body leakage current	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 25\text{ V}$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 3\text{ A}$		0.365	0.475	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{GS} = 0\text{ V}$, $V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$,	-	590	-	pF
C_{oss}	Output capacitance		-	27.5	-	pF
C_{rss}	Reverse transfer capacitance		-	1.1	-	pF
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{GS} = 0\text{ V}$, $V_{DS} = 0\text{ to }520\text{ V}$	-	168.5	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	6.5	-	Ω
Q_g	Total gate charge	$V_{DD} = 520\text{ V}$, $I_D = 10\text{ A}$, $V_{GS} = 10\text{ V}$ (see Figure 15)	-	17	-	nC
Q_{gs}	Gate-source charge		-	3.3	-	nC
Q_{gd}	Gate-drain charge		-	7	-	nC

1. $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 325\text{ V}$, $I_D = 5\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 14 and 19)	-	11	-	ns
t_r	Rise time		-	7.8	-	ns
$t_{d(off)}$	Turn-off delay time		-	38	-	ns
t_f	Fall time		-	12	-	ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		6.5	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		26	A
$V_{SD}^{(2)}$	Forward on voltage	$V_{GS} = 0\text{ V}$, $I_{SD} = 6.5\text{ A}$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 10\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$ (see Figure 16)	-	312		ns
Q_{rr}	Reverse recovery charge		-	2.7		μC
I_{RRM}	Reverse recovery current		-	17.5		A
t_{rr}	Reverse recovery time	$I_{SD} = 10\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 16)	-	464		ns
Q_{rr}	Reverse recovery charge		-	4		μC
I_{RRM}	Reverse recovery current		-	17.5		A

1. Pulse width limited by safe operating area

2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

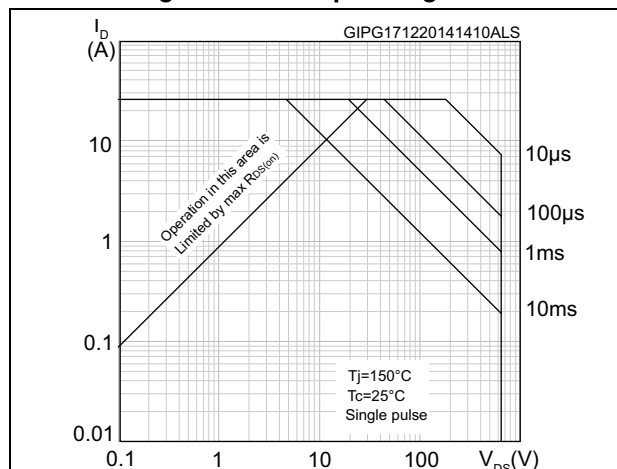


Figure 3. Thermal impedance

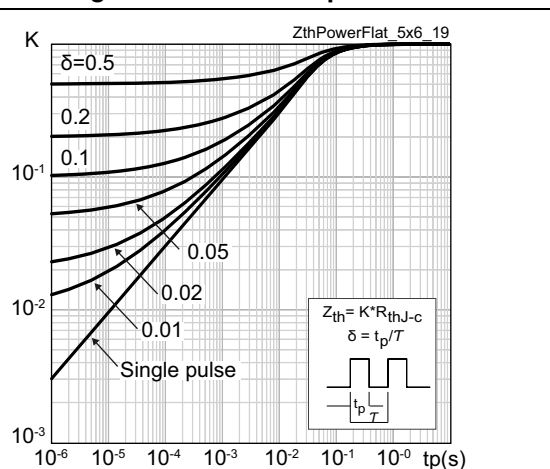


Figure 4. Output characteristics

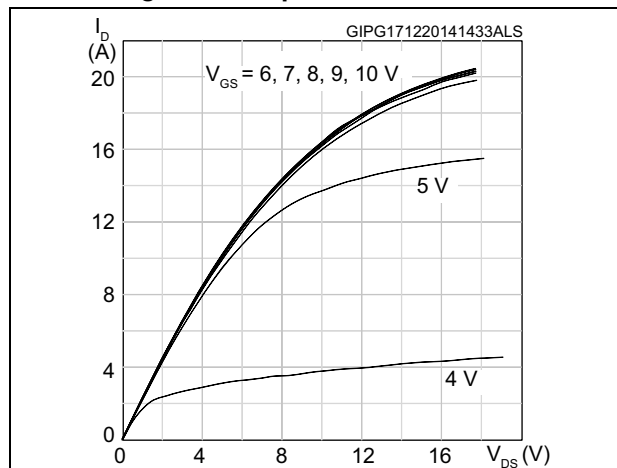


Figure 5. Transfer characteristics

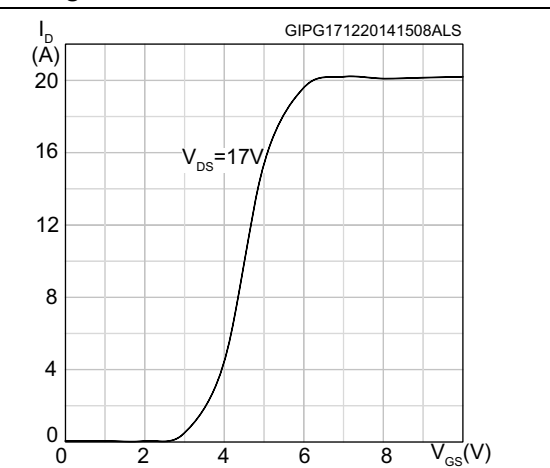
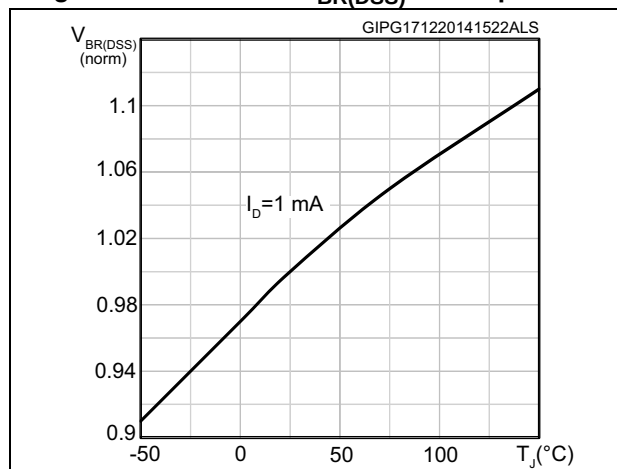
Figure 6. Normalized $V_{BR(DSS)}$ vs temperature

Figure 7. Static drain-source on-resistance

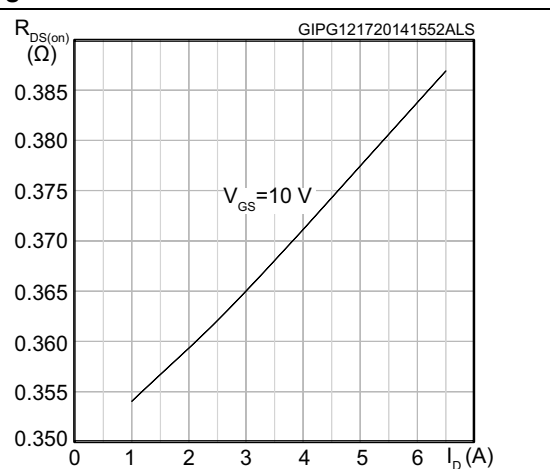


Figure 8. Gate charge vs gate-source voltage

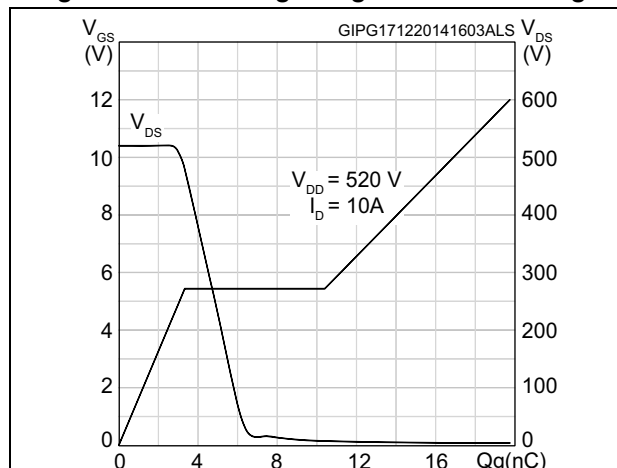


Figure 9. Capacitance variations

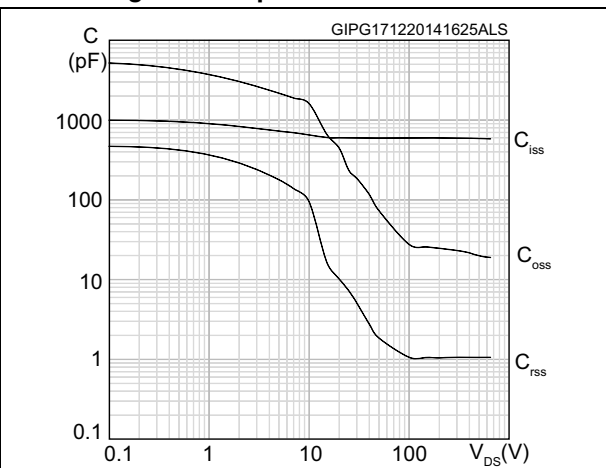


Figure 10. Normalized gate threshold voltage vs temperature

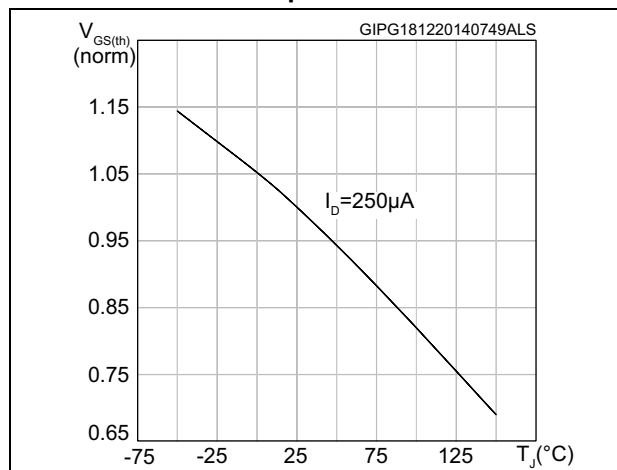


Figure 11. Normalized on-resistance vs temperature

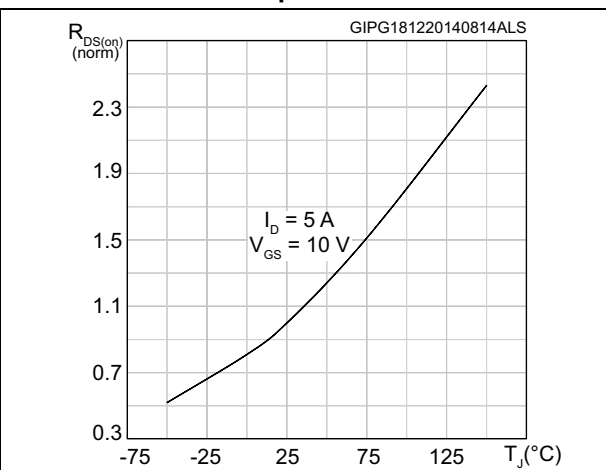


Figure 12. Source-drain diode forward characteristics

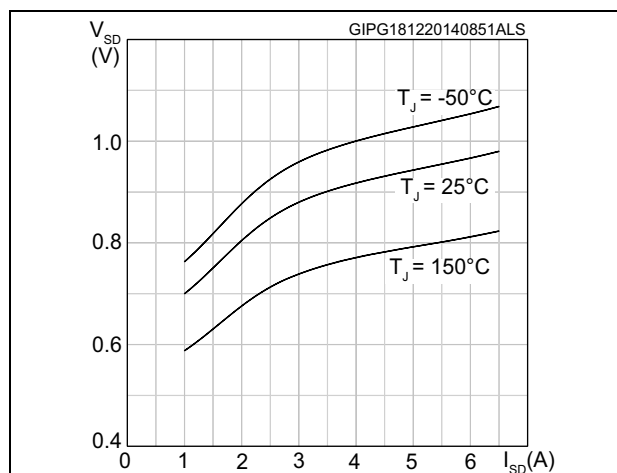
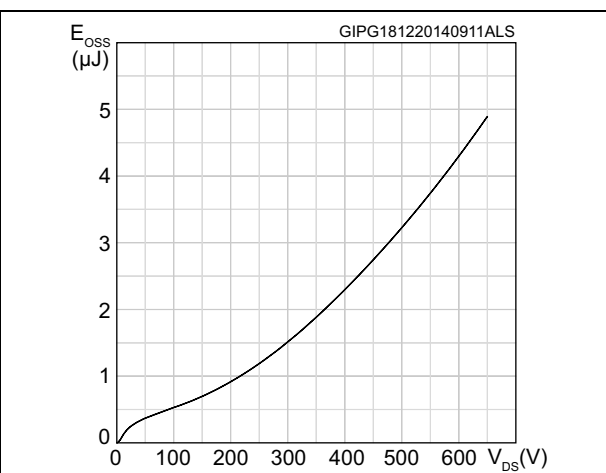


Figure 13. Output capacitance stored energy



3 Test circuits

Figure 14. Switching times test circuit for resistive load

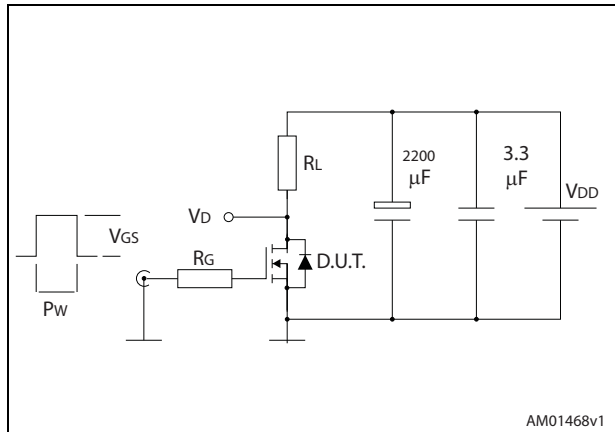


Figure 15. Gate charge test circuit

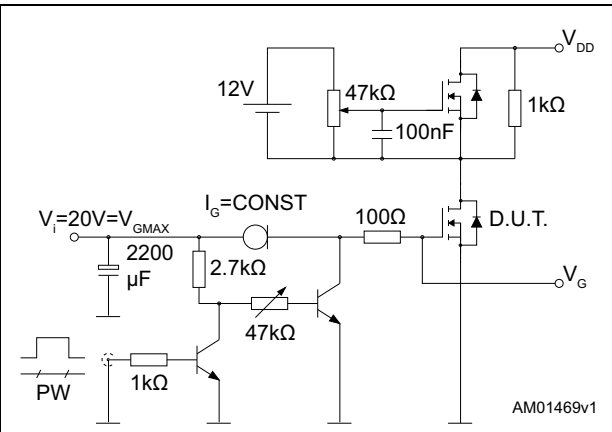


Figure 16. Test circuit for inductive load switching and diode recovery times

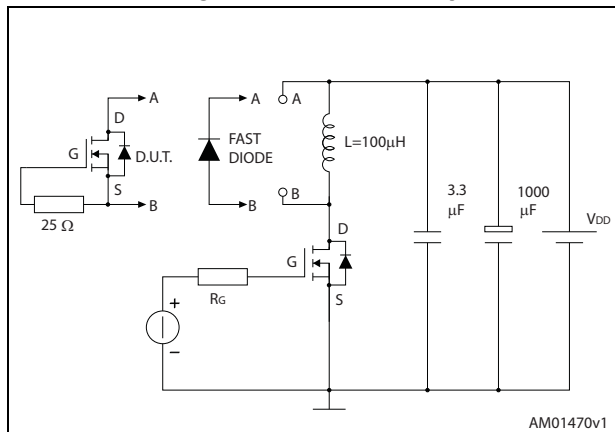


Figure 17. Unclamped inductive load test circuit

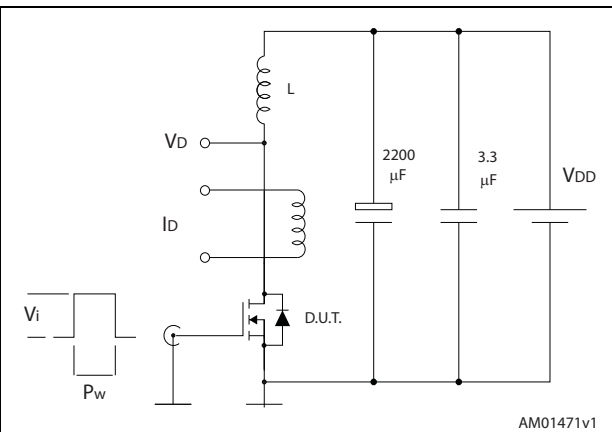


Figure 18. Unclamped inductive waveform

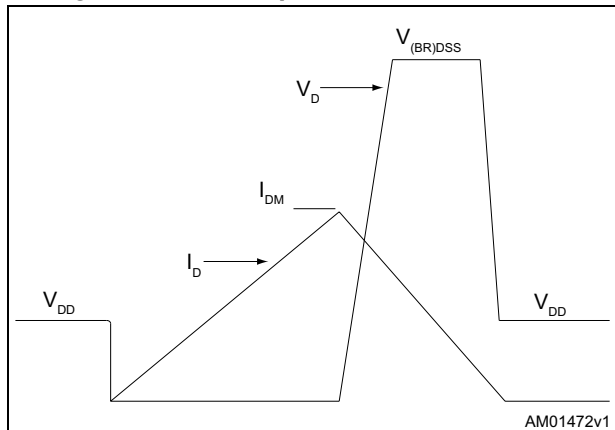
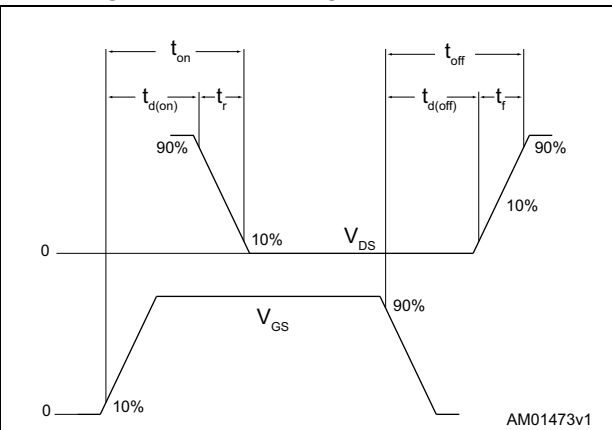


Figure 19. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Figure 20. PowerFLAT™ 5x6 HV drawing

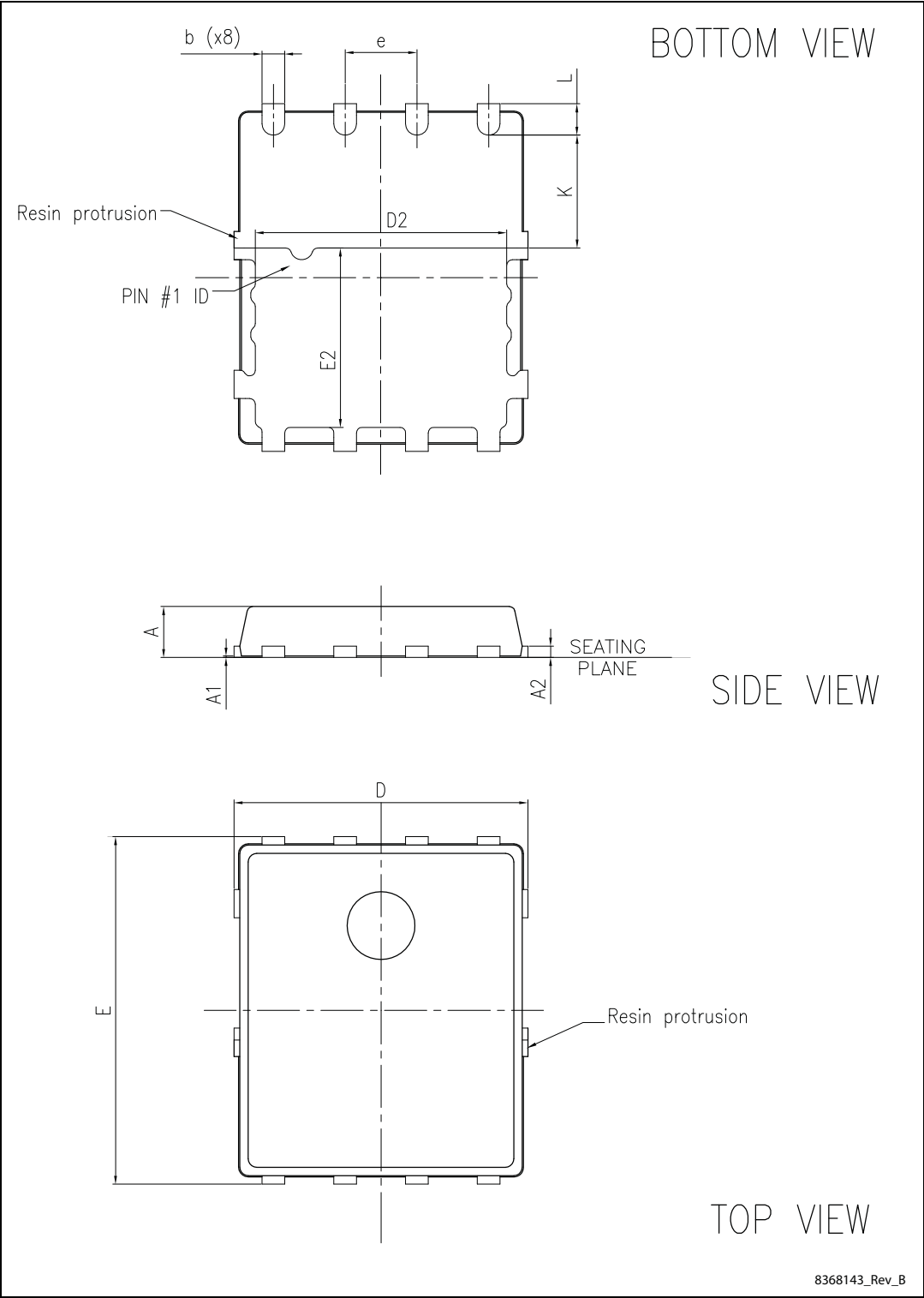


Figure 21. PowerFLAT™ 5x6 HV recommended footprint (dimensions are in mm)

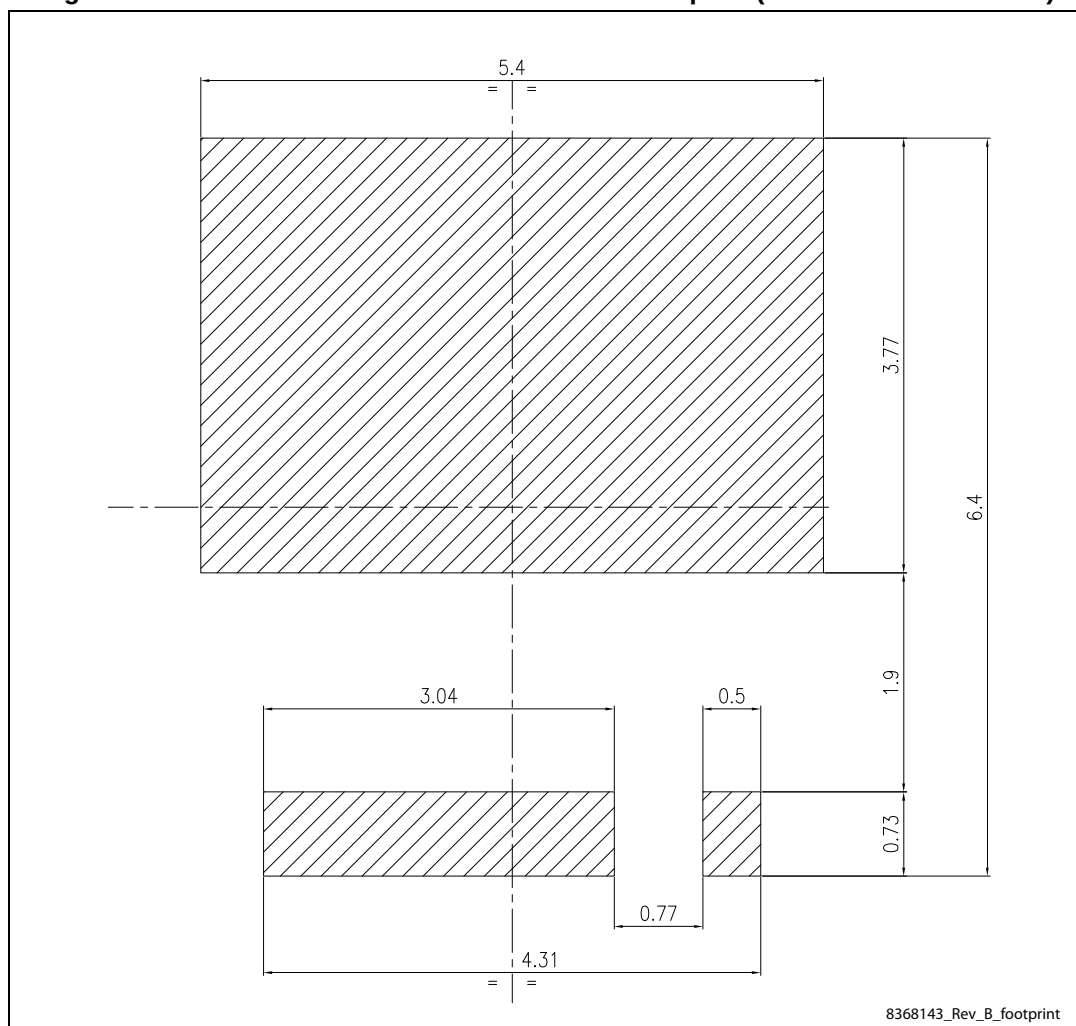


Table 9. PowerFLAT™ 5x6 HV mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80		1.00
A1	0.02		0.05
A2		0.25	
b	0.30		0.50
D	5.00	5.20	5.40
E	5.95	6.15	6.35
D2	4.30	4.40	4.50
E2	3.10	3.20	3.30
e		1.27	
L	0.50	0.55	0.60
K	1.90	2.00	2.10

5 Packaging mechanical data

Figure 22. PowerFLAT™ 5x6 tape^(a)

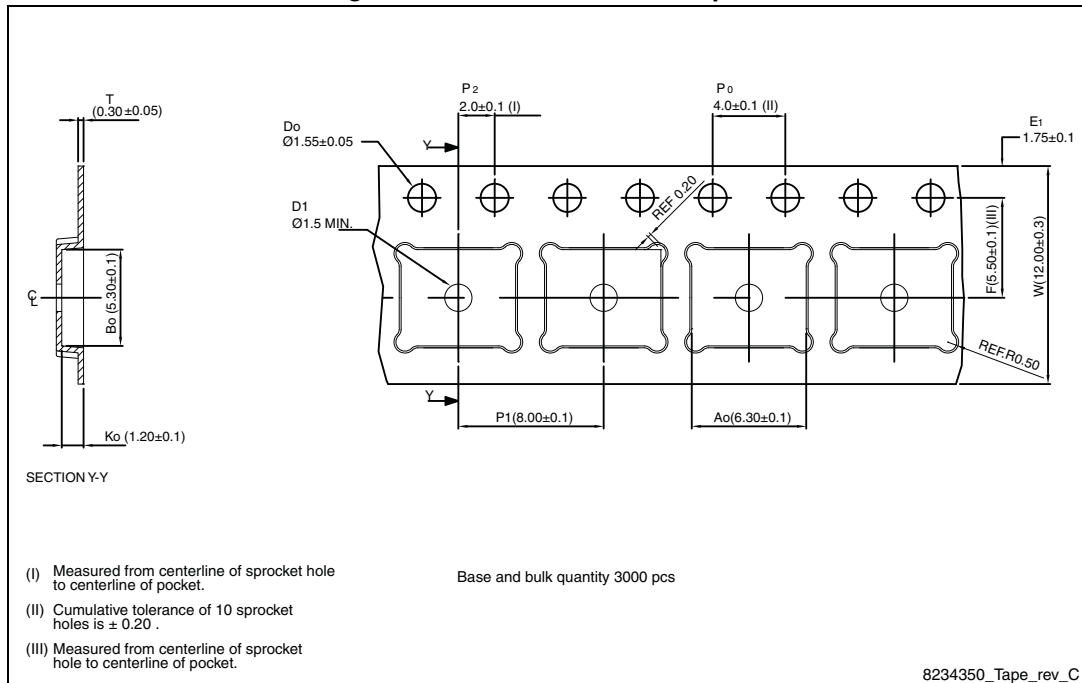
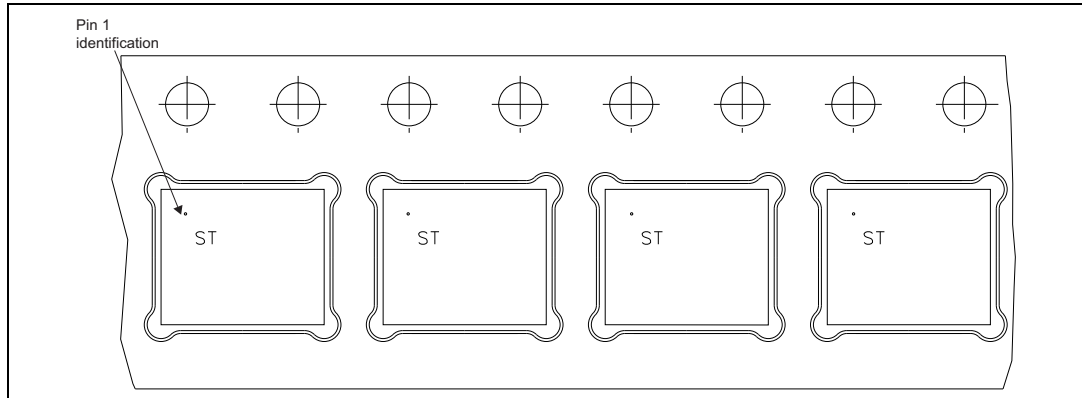
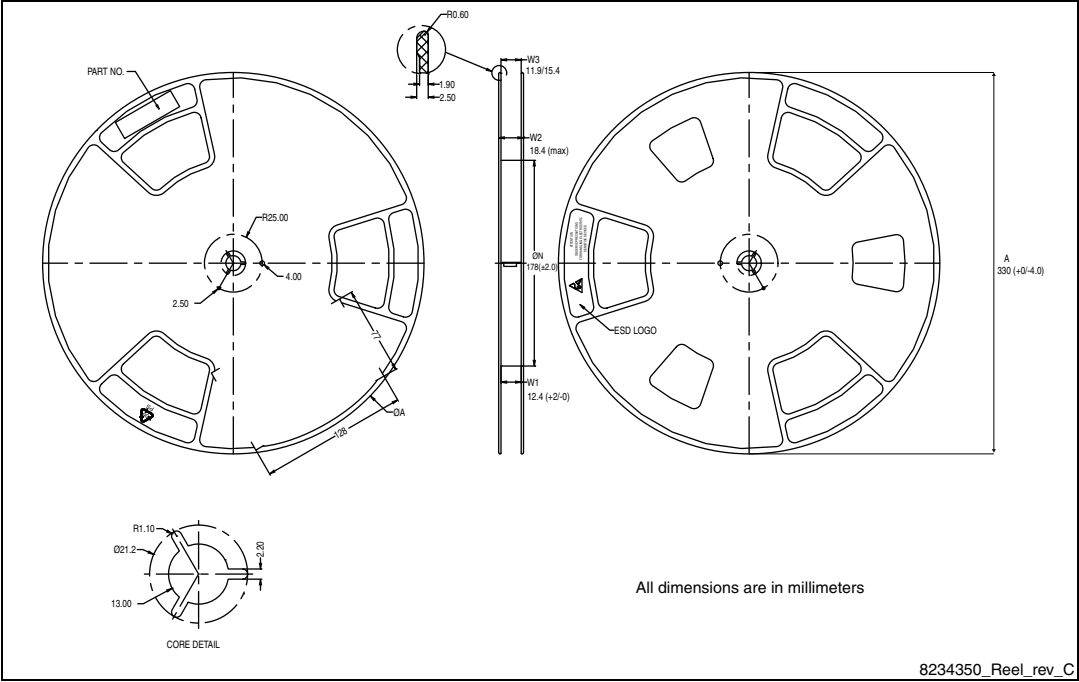


Figure 23. PowerFLAT™ 5x6 package orientation in carrier tape.



a. All dimensions are in millimeters.

Figure 24. PowerFLAT™ 5x6 reel



6 Revision history

Table 10. Document revision history

Date	Revision	Changes
18-Dec-2014	1	First release.

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